

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSIII)

# TPCS8302

Lithium Ion Battery Applications

Notebook PC Applications

Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain-source ON resistance:  $R_{DS(ON)} = 22 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 12 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = -10 \text{ }\mu\text{A}$  (max) ( $V_{DS} = -20 \text{ V}$ )
- Enhancement mode:  $V_{th} = -0.5 \sim -1.2 \text{ V}$  ( $V_{DS} = -10 \text{ V}$ ,  $I_D = -200 \text{ }\mu\text{A}$ )

## Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

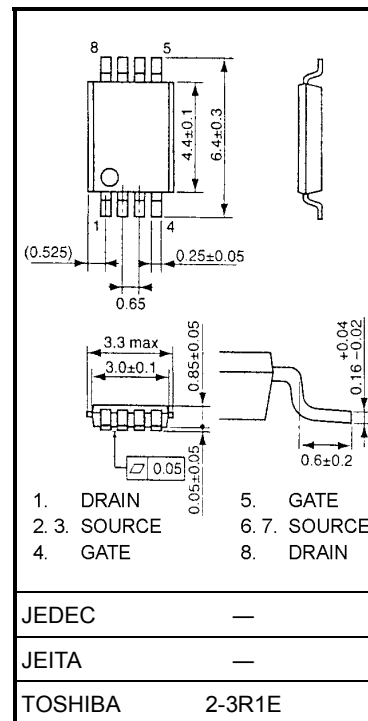
Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	-20	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		$V_{DGR}$	-20	V
Gate-source voltage		$V_{GSS}$	$\pm 12$	V
Drain current	DC (Note 1)	$I_D$	-5	A
	Pulse (Note 1)	$I_{DP}$	-20	
Drain power dissipation ( $t = 10 \text{ s}$ ) (Note 2a)	Single-device operation (Note 3a)	$P_D (1)$	1.1	W
	Single-device value at dual operation (Note 3b)	$P_D (2)$	0.75	
Drain power dissipation ( $t = 10 \text{ s}$ ) (Note 2b)	Single-device operation (Note 3a)	$P_D (1)$	0.6	W
	Single-device value at dual operation (Note 3b)	$P_D (2)$	0.35	
Single pulse avalanche energy (Note 4)		$E_{AS}$	32.5	mJ
Avalanche current		$I_{AR}$	-5	A
Repetitive avalanche energy Single-device value at dual operation (Note 2a, 3b, 5)		$E_{AR}$	0.075	mJ
Channel temperature		$T_{ch}$	150	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	-55~150	$^\circ\text{C}$

Note: (Note 1), (Note 2), (Note 3), (Note 4) and (Note 5): See next page.

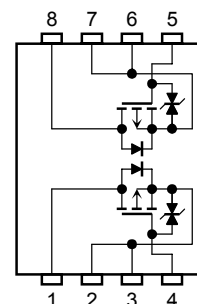
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Please handle with caution.

Unit: mm



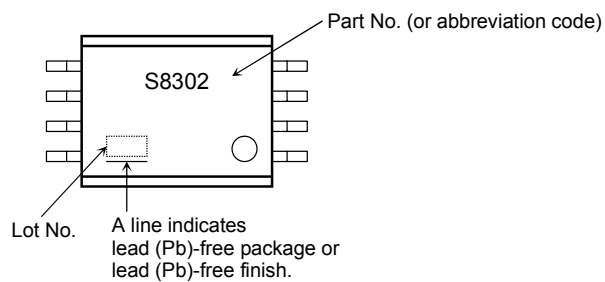
## Circuit Configuration



## Thermal Characteristics

Characteristics		Symbol	Max	Unit
Thermal resistance, channel to ambient ( $t = 10$ s) (Note 2a)	Single-device operation (Note 3a)	$R_{th(ch-a)}(1)$	114	$^{\circ}\text{C}/\text{W}$
	Single-device value at dual operation (Note 3b)	$R_{th(ch-a)}(2)$	167	
Thermal resistance, channel to ambient ( $t = 10$ s) (Note 2b)	Single-device operation (Note 3a)	$R_{th(ch-a)}(1)$	208	$^{\circ}\text{C}/\text{W}$
	Single-device value at dual operation (Note 3b)	$R_{th(ch-a)}(2)$	357	

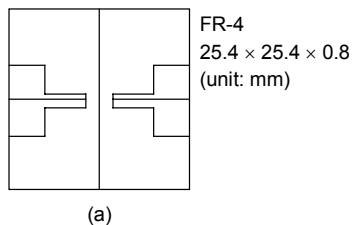
## Marking (Note 6)



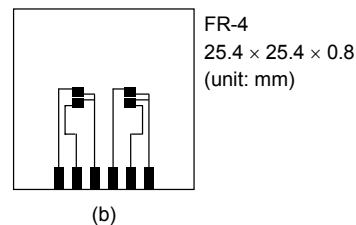
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:

a) Device mounted on a glass-epoxy board (a)



b) Device mounted on a glass-epoxy board (b)



Note 3:

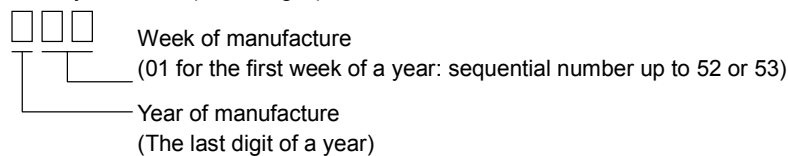
- The power dissipation and thermal resistance values are shown for a single device (During single-device operation, power is only applied to one device.)
- The power dissipation and thermal resistance values are shown for a single device (During dual operation, power is evenly applied to both devices.)

Note 4:  $V_{DD} = -16$  V,  $T_{ch} = 25^{\circ}\text{C}$ ,  $L = 1.0$  mH,  $I_{AR} = -5$  A,  $R_G = 25\ \Omega$

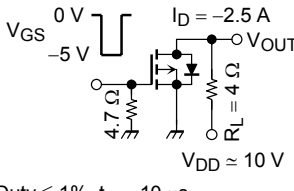
Note 5: Repetitive rating: pulse width limited by maximum channel temperature

Note 6:  $\circ$  on lower right of the marking indicates Pin 1.

※ Weekly code: (Three digits)

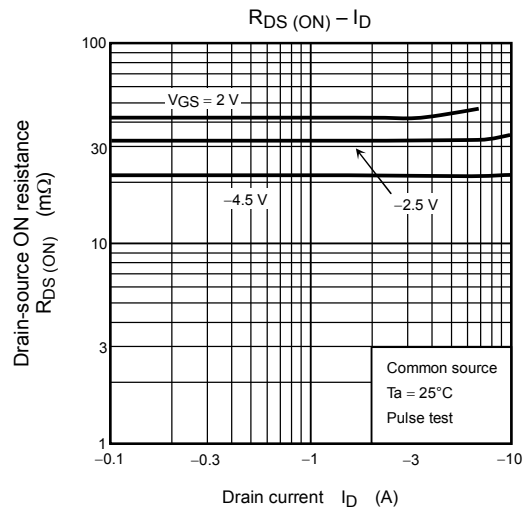
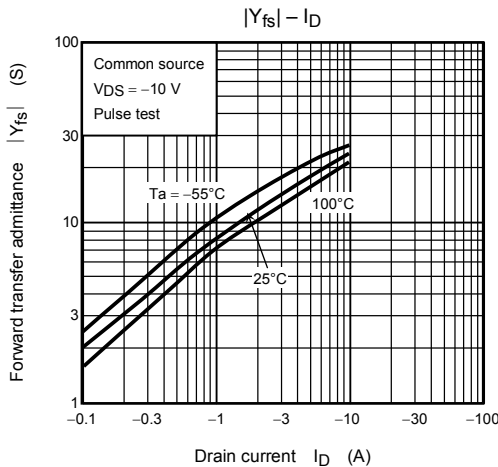
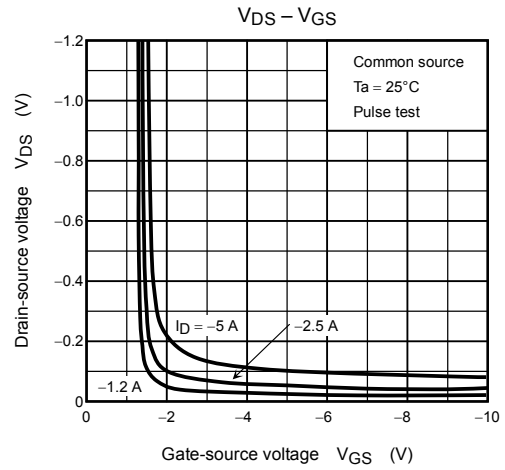
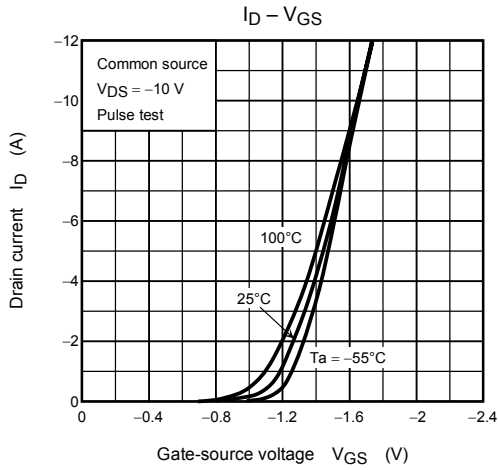
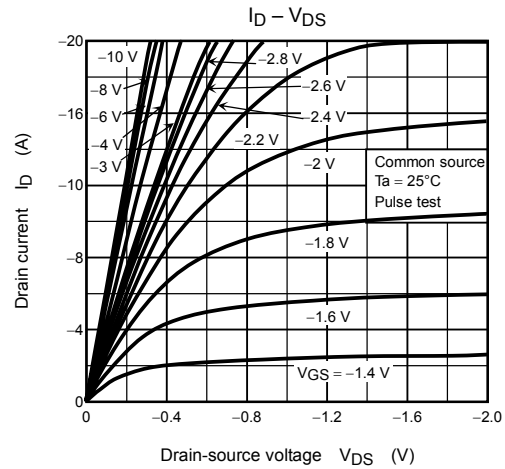
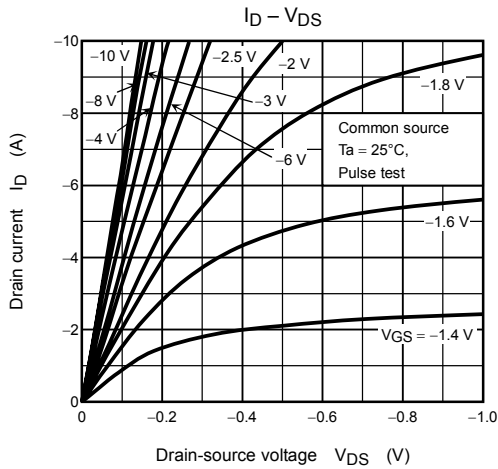


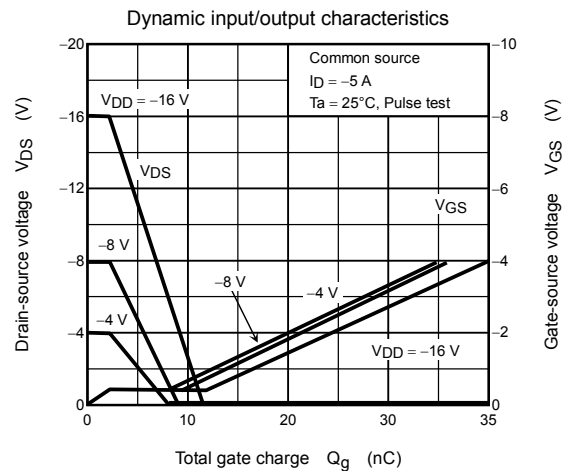
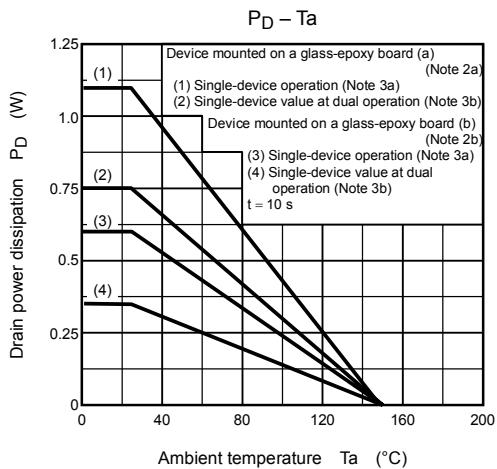
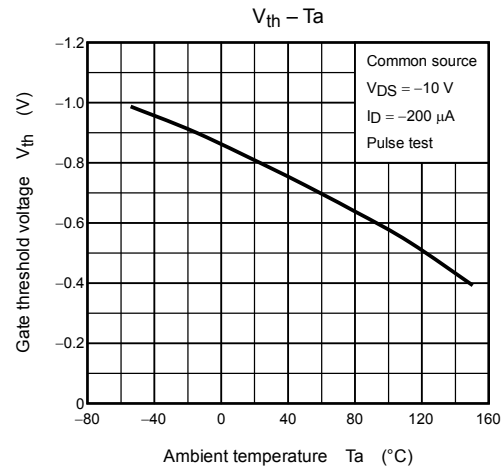
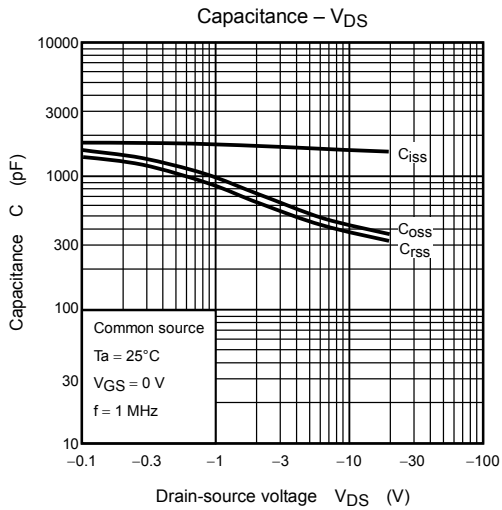
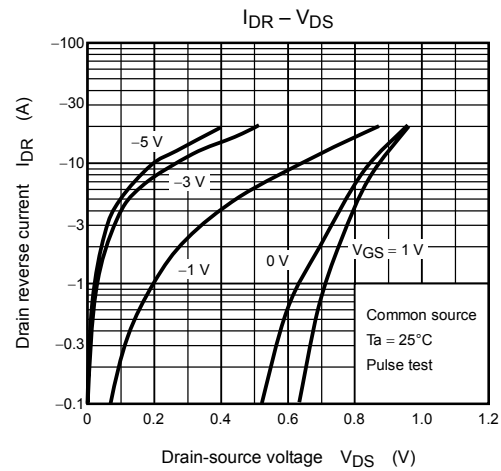
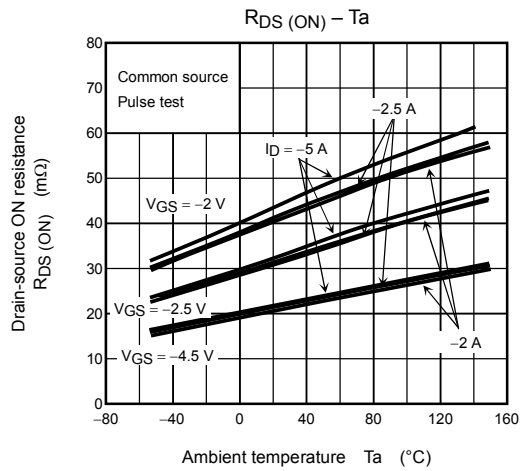
**Electrical Characteristics (Ta = 25°C)**

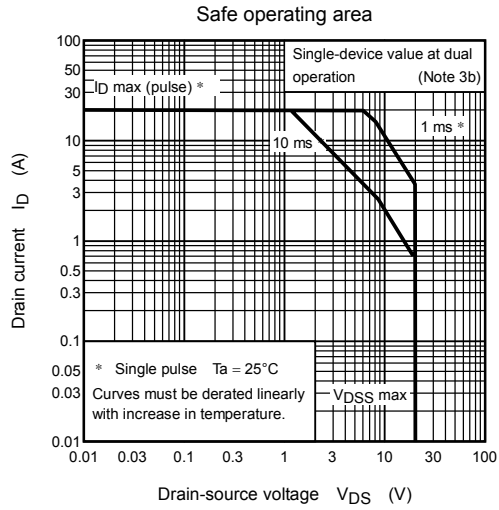
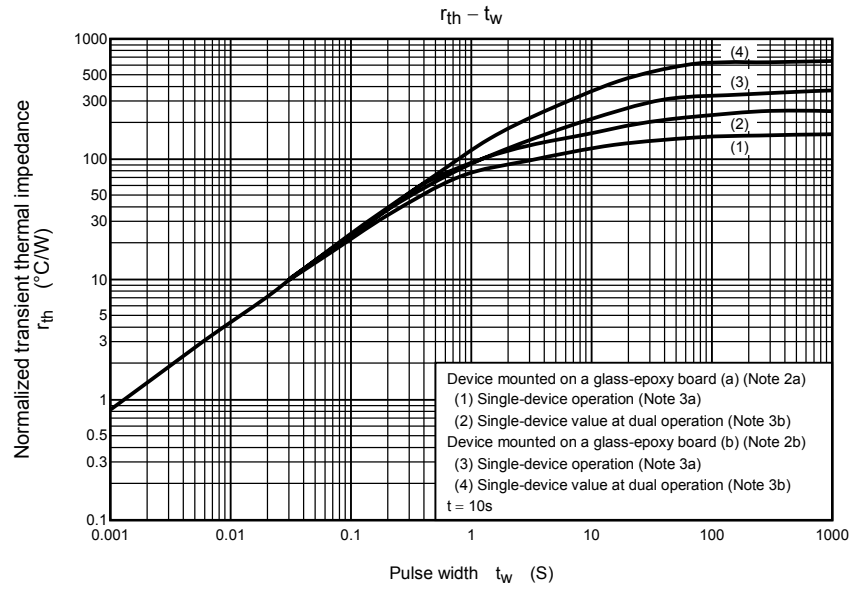
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-OFF current		$I_{DSS}$	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	-10	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR) DSS}$	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-20	—	—	V
		$V_{(BR) DSX}$	$I_D = -10 \text{ mA}, V_{GS} = 12 \text{ V}$	-8	—	—	
Gate threshold voltage		$V_{th}$	$V_{DS} = -10 \text{ V}, I_D = -200 \mu\text{A}$	-0.5	—	-1.2	V
Drain-source ON resistance		$R_{DS (ON)}$	$V_{GS} = -2.0 \text{ V}, I_D = -2.5 \text{ A}$	—	42	95	$\text{m}\Omega$
			$V_{GS} = -2.5 \text{ V}, I_D = -2.5 \text{ A}$	—	32	60	
			$V_{GS} = -4.5 \text{ V}, I_D = -2.5 \text{ A}$	—	22	35	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = -10 \text{ V}, I_D = -2.5 \text{ A}$	5.5	12	—	S
Input capacitance		$C_{iss}$	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	1590	—	pF
Reverse transfer capacitance		$C_{rss}$		—	380	—	
Output capacitance		$C_{oss}$		—	430	—	
Switching time	Rise time	$t_r$	 <p><math>V_{GS}</math> 0 V, -5 V  <math>I_D = -2.5 \text{ A}</math>  <math>V_{OUT}</math>  <math>4.7 \Omega</math>  <math>4 \Omega</math>  <math>V_{DD} \approx 10 \text{ V}</math>  Duty <math>\leq 1\%</math>, <math>t_w = 10 \mu\text{s}</math></p>	—	9	—	ns
	Turn-ON time	$t_{on}$		—	16	—	
	Fall time	$t_f$		—	45	—	
	Turn-OFF time	$t_{off}$		—	113	—	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 16 \text{ V}, V_{GS} = -5 \text{ V}, I_D = -5 \text{ A}$	—	28.5	—	nC
Gate-source charge 1		$Q_{gs}$		—	19	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	9.4	—	

**Source-Drain Ratings and Characteristics (Ta = 25°C)**

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	$I_{DRP}$	—	—	—	-20	A
Forward voltage (diode)		$V_{DSF}$	$I_{DR} = -5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	1.2	V







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